

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	28544	(silicon adj insulator soi silicon\$1on\$1insulat\$4)	US-PGPUB; USPAT	OR	ON	2006/10/12 16:28
L2	42	((source and drain)adj1 (extension ldd))with (metal silicide))	US-PGPUB; USPAT	OR	ON	2006/10/12 14:53
L3	24	((LDD)(low adj impurity))near4(extension))with (metal silicide)	US-PGPUB; USPAT	OR	ON	2006/10/12 15:09
L4	9	((metal silicide) near11(LDD low\$3 adj impurity)near14(extending extension penetrating))and 1	US-PGPUB; USPAT	OR	ON	2006/10/12 15:10
L5	364	((metal silicide) near11(body)near14(coupl\$4 \$3contact\$4))and 1	US-PGPUB; USPAT	OR	ON	2006/10/12 16:10
L6	138	((metal silicide) near3(body)near14(coupl\$4 \$3contact\$4))and 1	US-PGPUB; USPAT	OR	ON	2006/10/12 15:59
L7	55	(LDD low\$3 adj impurity extension)and 6	US-PGPUB; USPAT	OR	ON	2006/10/12 16:06
L8	29	"5949104"	US-PGPUB; USPAT	OR	ON	2006/10/12 15:34
L9	11	1 and 8	US-PGPUB; USPAT	OR	ON	2006/10/12 15:34
L10	11333	(silicon adj insulator soi silicon\$1on\$1insulat\$4)	EPO; JPO; DERWENT	OR	ON	2006/10/12 15:43
L11	27	((metal silicide) near11(body)near14(coupl\$4 \$3contact\$4))and 10	EPO; JPO; DERWENT	OR	ON	2006/10/12 16:22
L12	3896	257/281-282 257/489 257/347 43 8/98 438/167.ccls.	US-PGPUB; USPAT	OR	ON	2006/10/12 15:58
L13	6	2 and 12	US-PGPUB; USPAT	OR	ON	2006/10/12 15:59
L14	109	((metal silicide) near11(body)near14(coupl\$4 \$3contact\$4))and 12	US-PGPUB; USPAT	OR	ON	2006/10/12 16:00
L15	43	(LDD low\$3 adj impurity extension)and 14	US-PGPUB; USPAT	OR	ON	2006/10/12 16:11
L16	206	((metal silicide) near11(active channel)near14(coupl\$4 \$3contact\$4))and 12	US-PGPUB; USPAT	OR	ON	2006/10/12 16:26
L17	67	(LDD low\$3 adj impurity extension)and 16	US-PGPUB; USPAT	OR	ON	2006/10/12 16:42

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L18	60	17 not 15	US-PGPUB; USPAT	OR	ON	2006/10/12 16:11
L19	9	(schottky adj contact\$4 )and 10	EPO; JPO; DERWENT	OR	ON	2006/10/12 16:25
L20	2276	(schottky) near5 (active channel body epitaxial)	US-PGPUB; USPAT	OR	ON	2006/10/12 17:12
L21	535	(LDD low\$3 adj impurity extension)and 20	US-PGPUB; USPAT	OR	ON	2006/10/12 16:27
L22	20	(silicon adj insulator soi silicon\$1on\$1insulat\$4).ti. and 21	US-PGPUB; USPAT	OR	ON	2006/10/12 17:32
L23	12	"5930605"	US-PGPUB; USPAT	OR	ON	2006/10/12 16:29
L24	113	(silicon adj insulator soi silicon\$1on\$1insulat\$4) and 21	US-PGPUB; USPAT	OR	ON	2006/10/12 16:52
L25	1828	(silicon adj insulator soi silicon\$1on\$1insulat\$4) and 12	US-PGPUB; USPAT	OR	ON	2006/10/12 16:40
L26	1380	(LDD low\$3 adj impurity extension)and (schottky) adj (contact\$2 diode\$2)	US-PGPUB; USPAT	OR	ON	2006/10/12 16:42
L27	216	(LDD low\$3 adj impurity extension)same (schottky) adj (contact\$2 diode\$2)	US-PGPUB; USPAT	OR	ON	2006/10/12 16:43
L28	33	(silicon adj insulator soi silicon\$1on\$1insulat\$4) and 27	US-PGPUB; USPAT	OR	ON	2006/10/12 16:52
L29	761	((schottky) near5 (active channel body epitaxial)).ab,clm.	US-PGPUB; USPAT	OR	ON	2006/10/12 17:13
L30	18	((schottky) near5 (active channel body epitaxial))same (LDD low\$3 adj impurity extension)).ab,clm.	US-PGPUB; USPAT	OR	ON	2006/10/12 17:15
L31	87	((schottky) near5 (active channel body epitaxial))same (LDD low\$3 adj impurity extension))	US-PGPUB; USPAT	OR	ON	2006/10/12 17:18
L32	18	(silicon adj insulator soi silicon\$1on\$1insulat\$4) and 31	US-PGPUB; USPAT	OR	ON	2006/10/12 17:16
L33	25	((schottky) near5 (active channel body epitaxial))and (LDD low\$3 adj impurity extension))	EPO; JPO; DERWENT	OR	ON	2006/10/12 17:27
L34	56	(schottky) adj (diode contact)and (LDD low\$3 adj impurity extension)	EPO; JPO; DERWENT	OR	ON	2006/10/12 17:30
L35	46	34 not 33	EPO; JPO; DERWENT	OR	ON	2006/10/12 17:28
L36	4	(metal silicide)near3 ((schottky) adj (diode contact))and (LDD low\$3 adj impurity extension)	EPO; JPO; DERWENT	OR	ON	2006/10/12 17:31

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L37	229	(metal silicide)near3 ((schottky) adj (diode contact))and (LDD low\$3 adj impurity extension)	US-PGPUB; USPAT	OR	ON	2006/10/12 17:31
L38	34	(silicon adj insulator soi silicon\$1on\$1insulat\$4)and 37	US-PGPUB; USPAT	OR	ON	2006/10/12 17:32